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### (54) SURFACE ACOUSTIC WAVE DEVICE

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#### (57)ABSTRACT

A surface acoustic wave (SAW) device includes: a substrate; a finger portion of an interdigital transducer (IDT) electrode disposed on the substrate; a pad portion of the interdigital transducer electrode electrically connected to the finger portion; and a wiring electrode disposed on the pad portion. The wiring electrode includes a contact metal layer and an aluminum-based layer. The contact metal layer is disposed between the pad portion and the aluminum-based layer. The contact metal layer includes platinum, palladium, or gold.

